
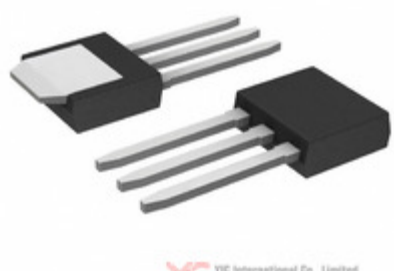





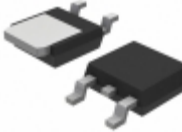
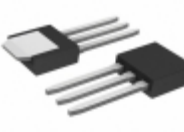

	NTD6600N-001
	Hersteller-Teilenummer: NTD6600N-001 Hersteller / Marke: AMI Semiconductor / ON Semiconductor Teil der Beschreibung: MOSFET N-CH 100V 12A IPAK Datenblätter:  NTD6600N-001.pdf RoHs Status: Enthält Blei / RoHS nicht konform Lagerzustand: New original, 5000 pcs Stock Available. Liefern von: Hong Kong Versandweg: DHL/Fedex/TNT/UPS/EMS
	
Image may be representation. See specs for product details.	

Spezifikationen

Teilenummer	NTD6600N-001
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 100V 12A IPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	5000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-251-3 Short Leads, IPak, TO-251AA
Supplier Device-Gehäuse	I-Pak
Verlustleistung (max)	1.28W (Ta), 56.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Ta)
Rds On (Max) @ Id, Vgs	146 mOhm @ 6A, 5V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	20nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	700pF @ 25V
Verpackung	Tube


















































NTD6600N-001 ist neu im Original, Suche NTD6600N-001 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NTD6600N-001 AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NTD6600N-001: Info@Y-IC.com

Sie können auch interessiert sein:

 NTD6N10 ON NTD6N10 ON	 NTD6N20ET4G ON ON SOT-252	 NTD6600G ON NTD6600G ON	 NTD65N03RT4 AMI Semiconductor / ON Semiconductor MOSFET N-CH 25V 9.5A DPAK
 NTD65N03RG AMI Semiconductor / ON Semiconductor MOSFET N-CH 25V 9.5A DPAK	 NTD6600N AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12A DPAK	 NTD6600N-1G AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12A IPAK	 NTD65N03RT4G AMI Semiconductor / ON Semiconductor MOSFET N-CH 25V 9.5A DPAK

heiße Teile

Mehr

 NTD6414AN	 NTD6414AN-1G	 NTD6414ANT4G	 NTD6414AUG	 NTD6415AN
 NTD6415AN-1G	 NTD6415ANL	 NTD6415ANLT4G	 NTD6415ANT4G	 NTD6416AN
 NTD6416AN-1G	 NTD6416ANG	 NTD6416ANL	 NTD6416ANL-1G	 NTD6416ANLT4G
 NTD6416ANT4G	 NTD65N03G	 NTD65N03R-001	 NTD65N03R-035	 NTD65N03R-1G
 NTD65N03R-35G	 NTD65N03RG	 NTD65N03RT4G	 NTD6600G	 NTD6600N
 NTD6600N-1G	 NTD6600NT4	 NTD6600NT4G	 NTD70N03	 NTD70N03R
 NTD70N03R-001	 NTD70N03R-1	 NTD70N03R-1G	 NTD70N03RG	 NTD70N03RT4
 NTD70N03RT4G	 NTD70N03TR4	 NTD78N03	 NTD78N03-001	 NTD78N03-035
 NTD78N03-1	 NTD78N03-1G	 NTD78N03-35G	 NTD78N03R-001	 NTD78N03R-1G
 NTD78N03RT4G	 NTD78N03T4	 NTD78N03T4G	 NTD80N02	 NTD80N02-001

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